



# Technical Data

## PST MTC175

### THYRISTOR MODULE

#### Features:

- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- Thyristor with amplifying gate

#### Typical applications:

- AC motor soft starters
- DC motor control (e.g. for machine tools)
- Temperature control (e.g. for ovens, chemical processes)

### ELECTRICAL CHARACTERISTICS AND RATINGS

#### Reverse blocking - Off-state

Device Type	$V_{RRM}$ (1)	$V_{DRM}$ (1)	$V_{RSM}$ (1)
PST MTC175	1600 V	1600 V	1700 V

$V_{RRM}$  = Repetitive peak reverse voltage

$V_{DRM}$  = Repetitive peak off-state voltage

$V_{RSM}$  = Non repetitive peak reverse voltage (2)

Repetitive reverse and off-state peak leakage current	$I_{RRM}, I_{DRM}$	40 mA (3)
Critical rate of rise of off-state voltage	$dv/dt$	1000 V/ $\mu$ s (4)

#### Notes:

All ratings are specified for  $T_j = 25^\circ\text{C}$  unless otherwise stated.

(1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range -40 to +125 °C.

(2) 10 ms max. pulse width

(3) Maximum value for  $T_j = T_{jmax}$

(4) Min. value for linear and exponential wave shape to 80% rated  $V_{DRM}$ . Gate open.  $T_j = T_{jmax}$

#### Conducting

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Average value of on-state current	$I_{T(AV)}$		175		A	50 Hz sine wave, 180° conduction, $T_c = 85^\circ\text{C}$
RMS value of on-state current	$I_{T(RMS)}$		275		A	50 Hz sine wave, 180° conduction, $T_c = 85^\circ\text{C}$
Surge non repetitive current	$I_{TSM}$		5.5		kA	50 Hz sine wave Half cycle $V_R = 0$ $T_j = 25^\circ\text{C}$
$I^2 t$	$I^2 t$		151		kA <sup>2</sup> s	
Peak on-state voltage	$V_{TM}$		1.80		V	On-state current 500 A, $T_j = 25^\circ\text{C}$
Threshold voltage	$V_{T(TO)}$		0.83		V	$T_j = T_{jmax}$
On-state slope resistance	$r_T$		1.30		mΩ	$T_j = T_{jmax}$
Holding current	$I_H$			400	mA	$T_j = 25^\circ\text{C}$
Latching current	$I_L$			1000	mA	$T_j = 25^\circ\text{C}$
Critical rate of rise of on-state current	$di/dt$		200		A/ $\mu$ s	$I_G = 5 I_{GT}$ , $t_r = 1 \mu\text{s}$ , $T_j = T_{jmax}$
RMS isolation voltage	$V_{INS}$		3000		V	AC 50 Hz, 60 s

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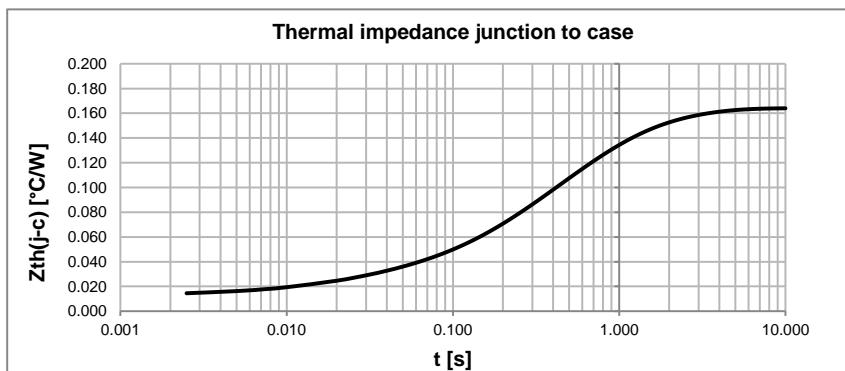
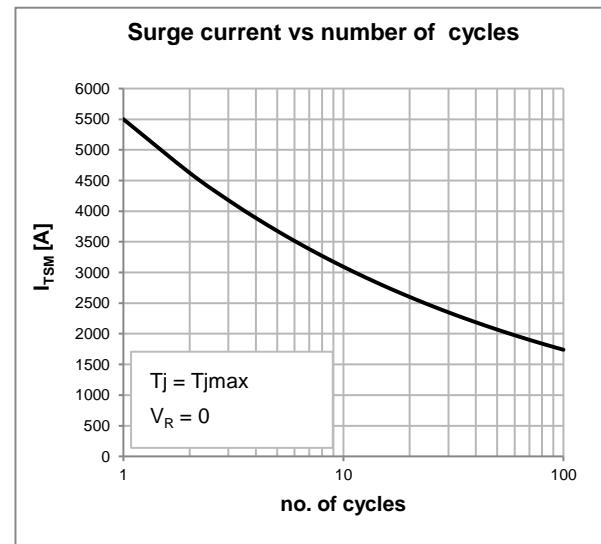
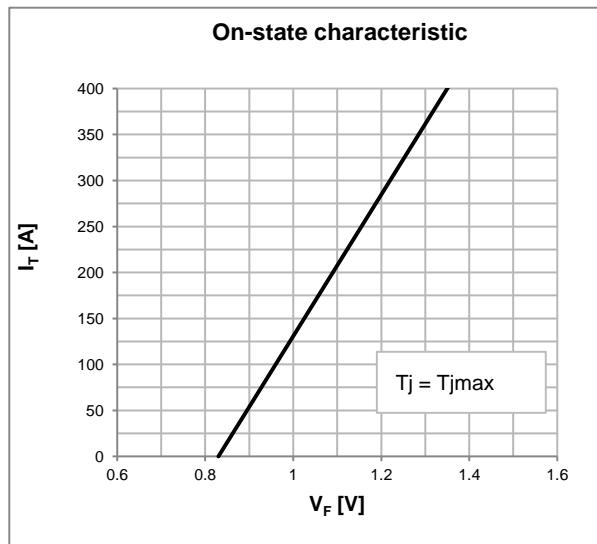
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### Triggering

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Gate current	$I_{GT}$		150		mA	$V_D = 6 \text{ V}$ ; $R_L = 3 \Omega$ ; $T_j = 25^\circ\text{C}$
Gate voltage	$V_{GT}$		2		V	$V_D = 6 \text{ V}$ ; $R_L = 3 \Omega$ ; $T_j = 25^\circ\text{C}$

### Thermal and mechanical characteristics and ratings

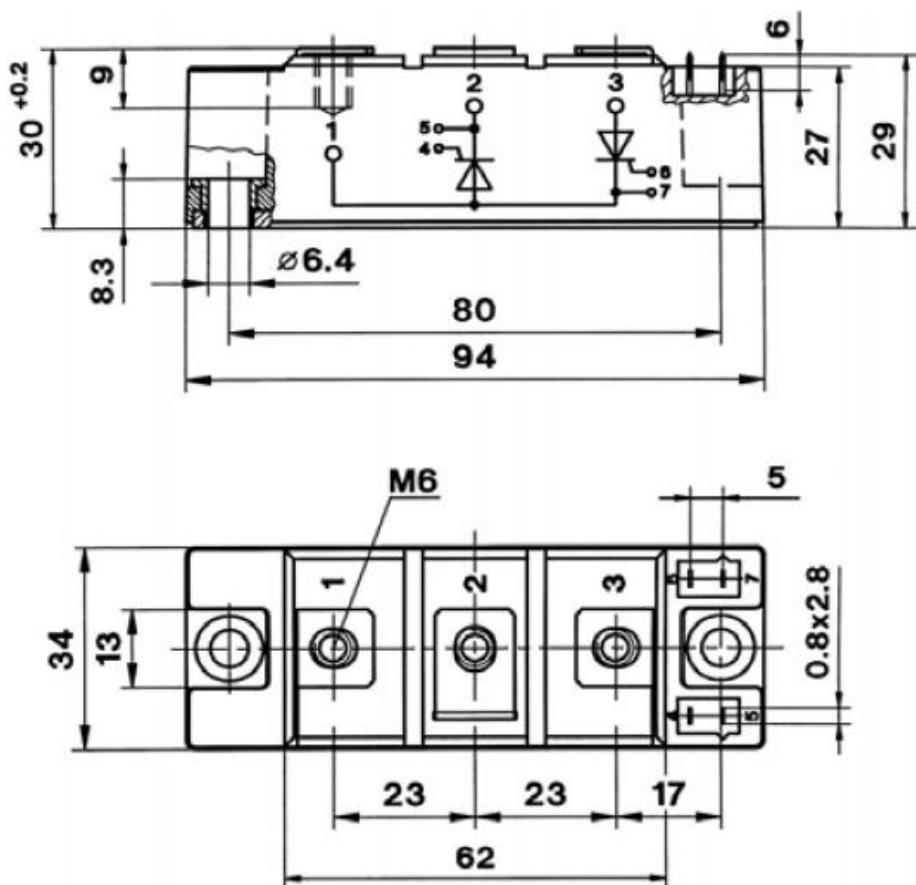
Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Operating temperature	$T_j$	-40	125		°C	
Storage temperature	$T_{stg}$	-40	125		°C	
Thermal resistance junction to case (per module)	$R_{th(j-c)}$		0.082	°C/W	SIN 180° conduction mounting surfaces smooth, flat and greased	
Thermal resistance case to sink (per module)	$R_{th(c-s)}$		0.050			
Mounting torque case-heatsink	$T$	4.5	5.5		N·m	
Mounting torque busbar-terminals	$T$	4.5	5.5		N·m	
Weight	$W$			170	g	



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## **THYRISTOR MODULE**

## **OUTLINE AND DIMENSIONS**



(all dimensions in mm)